

wherein said protruding portion is formed only in a region other than a region directly below said conductive layer wiring.

5. (Twice Amended) A semiconductor device comprising:

a substrate which has an inductor region;

a protruding portion which is formed on the top face of the substrate;

a conductive layer wiring which is formed in said inductor region on the substrate so as to have a spiral shape and which serves as an induction element; and

a protective film which is formed in said inductor region between the substrate and said conductive layer and prevents silicidation of said protruding portion in said inductor region.

7. (Twice Amended) A semiconductor device as set forth in claim 6, which further comprises an extracting wiring which is connected to said conductive layer wiring.

10. (Thrice Amended) A semiconductor device as set forth in claim 5, wherein said protruding portion is formed exclusively in a region other than a region directly below said conductive layer wiring.

12. (Twice Amended) A semiconductor device as set forth in claim 11, which further comprises an extracting wiring which is connected to said conductive layer wiring.

Please add new Claims 21-23 as follows:

21. (New) A semiconductor device comprising:

a substrate;
a protruding portion which is formed on the top face of the substrate and the top of which serves as a dummy element for controlling a chemical mechanical polishing process; and

a conductive layer wiring which is formed on the substrate so as to have a spiral shape and which serves as an induction element,

wherein said protruding portion is formed only in a region other than a region directly below said conductive layer wiring.

22. (New) A semiconductor device comprising:

a substrate which has an inductor region;
a protruding portion which is formed on the top face of the substrate;
a conductive layer wiring which is formed in said inductor region on the substrate so as to have a spiral shape and which serves as an induction element; and
a protective film which is formed only in said inductor region between the substrate and said conductive layer and prevents silicidation of said protruding portion in said inductor region.

23. (New) A semiconductor device comprising:

a substrate which has a first region for an induction element and a second region for an active element;
a protruding portion which is formed on the top face of the substrate;